# 50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

14 September 2018

Product data sheet

# 1. General description

NPN/PNP Resistor-Equipped double Transistors (RET) in an ultra small DFN1412-6 (SOT1268) leadless Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PRMH12.

# 2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- · Simplifies circuit design
- · Reduces component count
- · Reduces pick and place costs
- Low package height of 0.5 mm
- AEC-Q101 qualified

# 3. Applications

- Digital applications
- Cost-savings alternative to BC847/BC857 series digital applications
- · Control of IC inputs
- · Switching loads

# 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor, for the PNP transistor with negative polarity								
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	50	V	
Io	output current			-	-	100	mA	
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}; T_{amb} = 25 \text{ °C}$		80	-	-		
R1	bias resistor 1	T <sub>amb</sub> = 25 °C	[1]	33	47	61	kΩ	
R2/R1	bias resistor ratio		[1]	0.8	1	1.2		

[1] See section "Test information" for resistor calculation and test conditions.



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# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1	7 6	
3	O2	output (collector) TR2	2 5	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2	3 8 4	TR1 R2 R1
6	01	output (collector) TR1		
7	01	output (collector) TR1	Transparent top view	
8	O2	output (collector) TR2	DFN1412-6 (SOT1268)	GND1 I1 O2 aaa-007379

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package		
	Name	Description	Version
PRMD12		plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body: 1.4 mm x 1.2 mm x 0.47 mm	SOT1268

# 7. Marking

### **Table 4. Marking codes**

Type number	Marking code
PRMD12	B2

# 50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

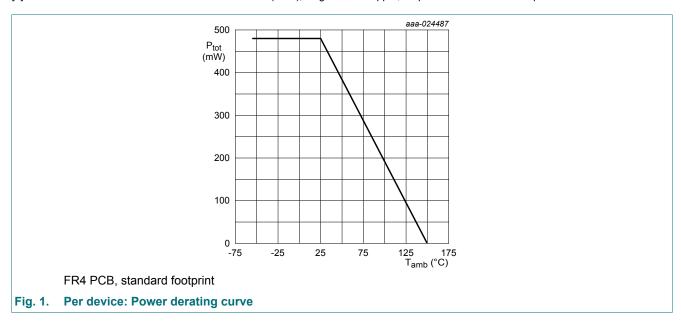
# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or, for the PNP transistor wit	n negative polarity				
V <sub>CBO</sub>	collector-base voltage	open emitter		-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	50	V
$V_{EBO}$	emitter-base voltage	open collector		-	10	V
VI	input voltage	positive		-	40	V
		negative		-	-10	V
Io	output current			-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	325	mW
Per device						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	480	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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# 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	385	K/W
Per device	Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	261	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

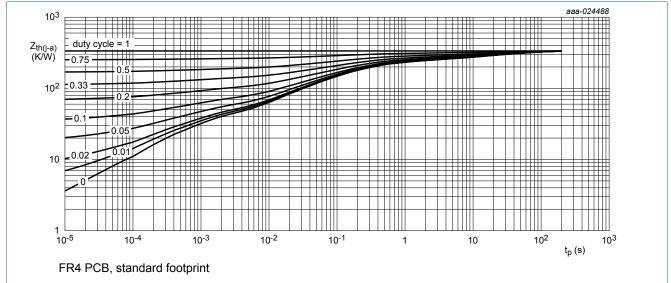


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or, for the PNP transistor v	vith negative polarity					
I <sub>CEO</sub>	collector-emitter cut-off	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	1	μΑ
	current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C			-	5	μΑ
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	90	μΑ
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 5 mA; T <sub>amb</sub> = 25 °C		80	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	150	mV
V <sub>I(off)</sub>	off-state input voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 μA; T <sub>amb</sub> = 25 °C		-	1.2	0.8	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE}$ = 0.3 V; $I_{C}$ = 2 mA; $T_{amb}$ = 25 °C		3	1.6	-	V
R1	bias resistor 1	T <sub>amb</sub> = 25 °C	[1]	33	47	61	kΩ
R2/R1	bias resistor ratio		[1]	0.8	1	1.2	
C <sub>C</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C		-	-	2.5	pF
		$V_{CB}$ = -10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C		-	-	3	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = 5 V; $I_{C}$ = 10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	[2]	-	230	-	MHz
		$V_{CE}$ = -5 V; $I_{C}$ = -10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	[2]	-	180	-	MHz

- [1] See section "Test information" for resistor calculation and test conditions.
- [2] Characteristics of built-in transistor.

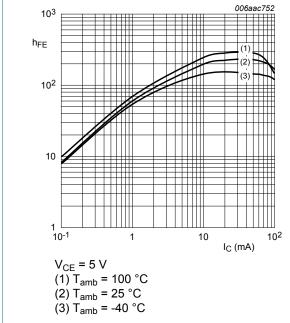


Fig. 3. NPN transistor: DC current gain as a function of collector current; typical values

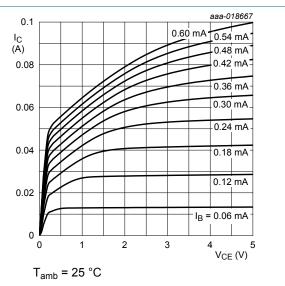
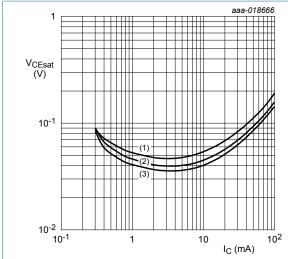


Fig. 4. NPN Transistor: Collector current as a function of collector-emitter voltage; typical values

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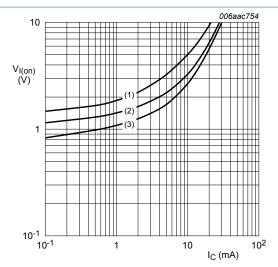


$$I_{\rm C}/I_{\rm B} = 20$$

$$(1) T_{amb} = 100 ° ($$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

Fig. 5. **NPN Transistor: Collector-emitter saturation** voltage as a function of collector current; typical values



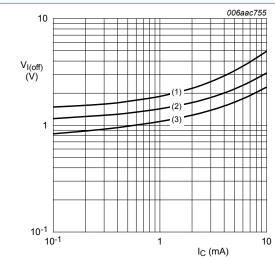
$$V_{CE} = 0.3 V$$

$$V_{CE} = 0.3 \text{ V}$$
(1)  $T_{amb} = -40 \text{ °C}$ 
(2)  $T_{amb} = 25 \text{ °C}$ 
(3)  $T_{amb} = 100 \text{ °C}$ 

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. NPN transistor: On-state input voltage as a function of collector current; typical values



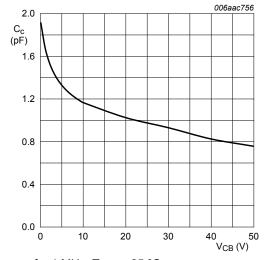
$$V_{CE} = 5 V$$

$$(1) T_{amb} = -40 °C$$

$$(2) T_{amb} = 25 °C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

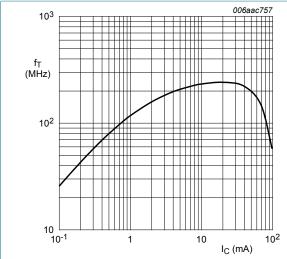
Fig. 7. NPN transistor: Off-state input voltage as a function of collector current; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$ 

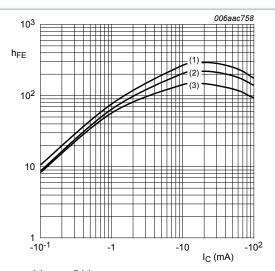
Fig. 8. NPN transistor: Collector capacitance as a function of collector-base voltage; typical

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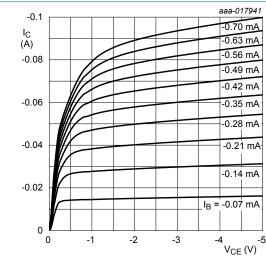
 $V_{CE}$  = 5 V;  $T_{amb}$  = 25 °C

Fig. 9. NPN transistor: Transition frequency as a function of collector current; typical values of built-in transistor



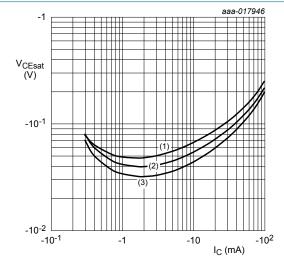
V<sub>CE</sub> = -5 V (1) T<sub>amb</sub> = 100 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -40 °C

Fig. 10. PNP transistor: DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

Fig. 11. PNP transistor: Collector current as a function of collector-emitter voltage; typical values



 $I_C / I_B = 20$ 

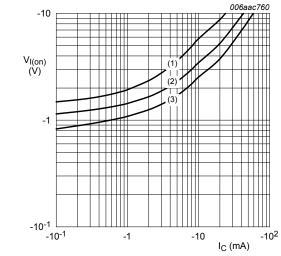
(1)  $T_{amb}$  = 100 °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

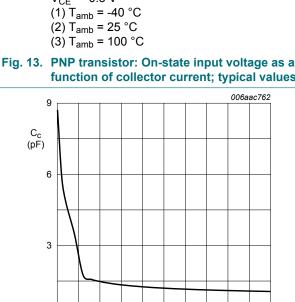
Fig. 12. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values

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 $V_{CE}$  = -0.3 V

function of collector current; typical values

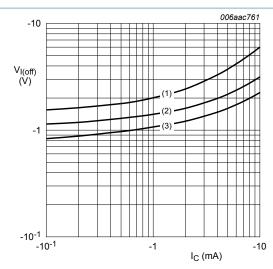


 $f = 1 MHz; T_{amb} = 25 °C$ 

-10

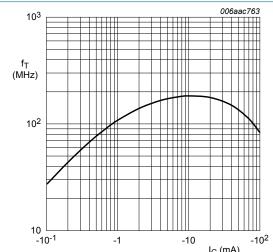
Fig. 15. PNP transistor: Collector capacitance as a function of collector-base voltage; typical values

-40 --V<sub>CB</sub> (V)



V<sub>CE</sub> = -5 V (1) T<sub>amb</sub> = -40 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 100 °C

Fig. 14. PNP transistor: Off-state input voltage as a function of collector current; typical values



 $V_{CE}$  = -5 V; f = 100 MHz;  $T_{amb}$  = 25 °C

Fig. 16. PNP transistor: Transition frequency as a function of collector current; typical values of built-in transistor

#### 50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

# 11. Test information

#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

#### **Resistor calculation**

· Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I12) - V(I11)}{I12 - I11}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

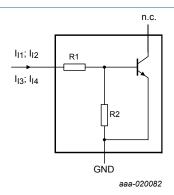


Fig. 17. NPN transistor: Resistor test circuit

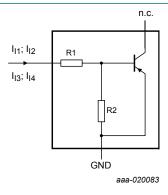


Fig. 18. PNP transistor: Resistor test circuit

#### **Resistor test conditions**

#### **Table 8. Resistor test conditions**

Per transistor; for the PNP transistor with negative polarity

R1 (kΩ)	R2 (kΩ)	Test conditions	est conditions				
		I <sub>I1</sub>	I <sub>12</sub>	I <sub>13</sub>	I <sub>14</sub>		
47	47	55 µA	105 μΑ	-55 µA	-150 μA		

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# 12. Package outline

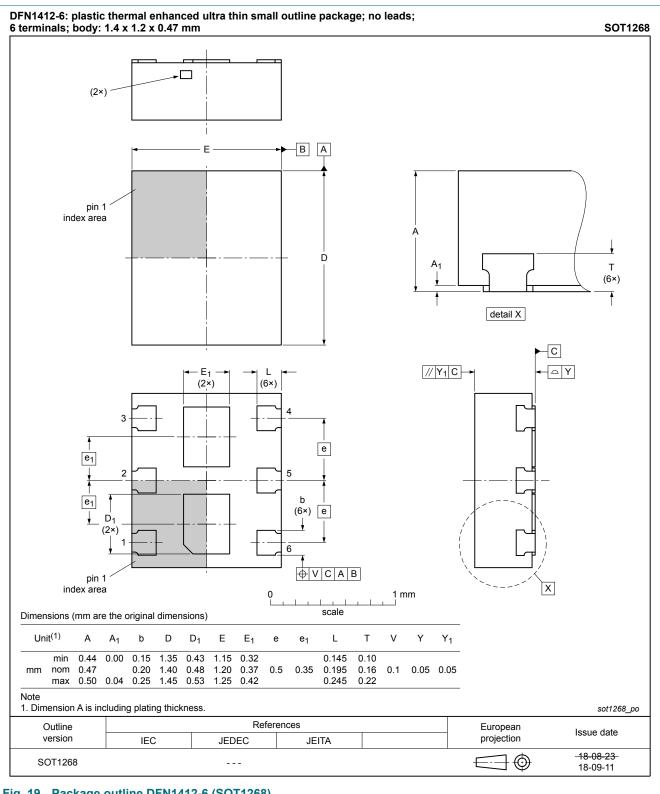
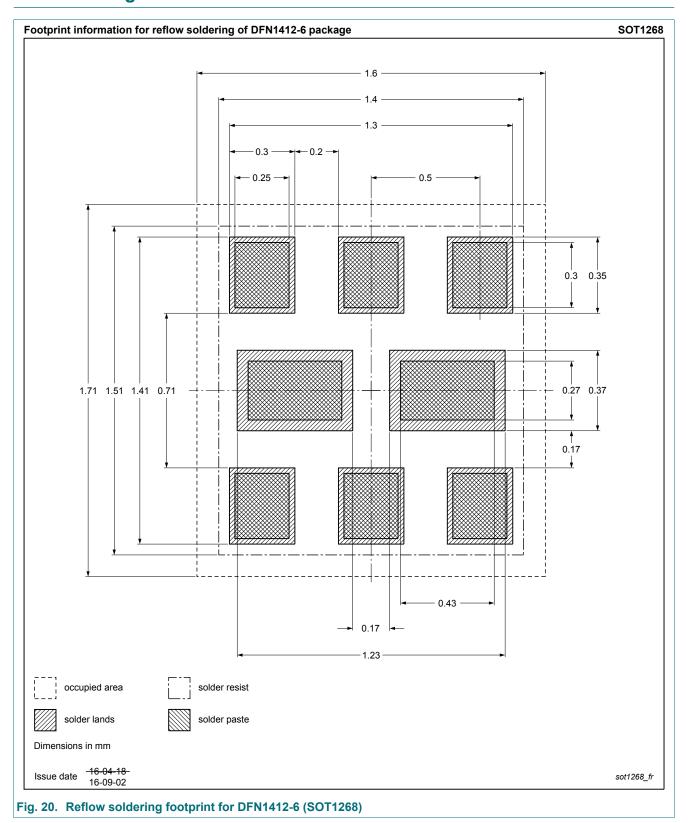


Fig. 19. Package outline DFN1412-6 (SOT1268)

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# 13. Soldering



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# 14. Revision history

### Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PRMD12 v.2	20180914	Product data sheet	-	PRMD12 v.1		
Modifications:	<ul> <li>Package outline</li> </ul>	Package outline drawing updated: Unit T added				
PRMD12 v.1	20170711	Product data sheet	-	-		

#### 50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

# 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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